





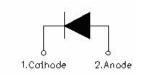
SDURK20FU60 ULTRAFAST RECTIFIER



Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Circuit Diagram



Features

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- This is a Pb Free Device
- Terminals finish: 100% Pure Tin
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Maximum Ratings@TA=25°C unless otherwise specified

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	600	V
Average Rectified Forward Current in DC	I _{F (AV)}	Tc=76°C	20	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse	130	Α

- China Germany Korea Singapore United States
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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop *	V _{F1}	@20A, Pulse, T _J = 25°C	1.98	2.5	V
	V _{F2}	@20A, Pulse, T _J = 125°C	1.69	2.3	V
Reverse Current *	I _{R1}	$@V_R = \text{rated } V_R$, $T_J = 25^{\circ}C$	0.02	10	μA
	I _{R2}	$@V_R = \text{rated } V_R$, $T_J = 125^{\circ}C$	8	500	uA
Reverse Recovery Time	t _{rr}	I _F =500mA, I _R =1A,and I _{rm} =250mA	20	30	ns
Reverse Recovery Time	t _{rr}	L = 20A diF/dt = 200A/v.a	23	-	ns
Reverse Recovery Charge	Qrr	$I_F = 20A$, diF/dt = 200A/µs $V_R = 400V$, $T_J = 25^{\circ}C$	39	-	nC
Reverse Recovery Current	I _{RRM}	VR = 400V, TJ = 25 C	3.2	-	Α
Reverse Recovery Time	t _{rr}	I _F = 20A, diF/dt = 200A/μs	76.5	-	ns
Reverse Recovery Charge	Q_{rr}	$V_R = 400V, T_J = 125^{\circ}C$	250	-	nC
Reverse Recovery Current	I _{RRM}		5.8	-	A

^{*} Pulse width < 300 µs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	2.5	°C/W
Approximate Weight	wt	-	1.6	g
Case Style	ITO-220AC-2L			





500

600



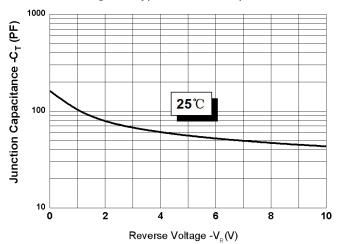
Ratings and Characteristics Curves

Figure 1 Typical Forward Characteristics Instantaneous Forward Current -I_F(A) **125**℃ 25℃ 2.0 1.4 Forward Voltage -V_F(V)

Figure 2 Typical Reverse Characteristics Instantaneous Reverse Current -I_R(uA) 125℃ 10¹ 10⁻¹ 25℃ 10. 10^{.3} 200

Figure 3 Typical Junction Capacitance

Reverse Voltage -V_R(V)



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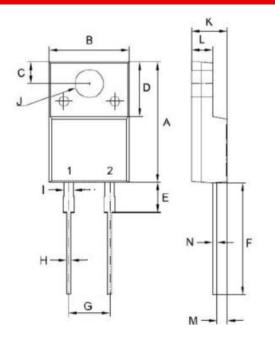
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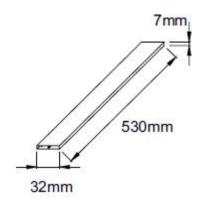


Mechanical Dimensions ITO-220AC-2L

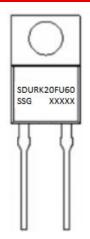


	Millimeters			
SYMBOL	MIN.	TYP.	MAX.	
A	14.80	15.00	15.20	
В	9.80	10.00	10.20	
C	2.50	2.70	2.90	
D	6.55	6.75	6.95	
Е	3.65	3.85	4.05	
F	13.30	13.50	13.70	
G	4.85	5.05	5.25	
Н	0.40	0.60	0.80	
I	1.10	1.30	1.50	
J	3.25	3.45	3.65	
K	4.25	4.45	4.65	
L	2.52	2.72	2.92	
M	1.09	1.29	1.49	
N	0.47	0.55	0.63	

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

 SDUR
 = Device Type

 K
 = Package type

 20
 = Forward Current (20A)

 FU
 = FU

 60
 = Reverse Voltage (600V)

 SSG
 = SSG

 YY
 = Year

YY = Year WW = Week L = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping	
SDURK20FU60	ITO-220AC-2L (Pb-Free)	50 pcs/ tube	

- China Germany Korea Singapore United States
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